

Descriptions

N-channel Double MOSFET in a SOT23-6 Plastic Package. It is ESD protested.

Features

advanced trench technology to provide excellent RDS(on), low gate charge.

 $V_{DSS}\text{=}20V \ / \ V_{GSS}\text{=}\pm12V \quad I_{D}\text{=}7A$

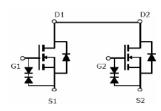
 $R_{DS(ON)}\text{=}16m\Omega(typ.)@V_{GS}\text{=}4.5V$

 $R_{DS(ON)}\text{=}19m\Omega(typ.)@V_{GS}\text{=}2.5V$

Applications

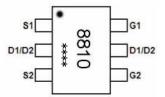
Use as Load Switch or PWM application.

Equivalent Circuit



Pinning





Absolute Maximum Ratings(T_a =25°C)

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Drain Current - Continuous	I _D (T _a =25℃)	7.0	Δ.	
Drain Current - Continuous	I _D (T _a =70℃)	5.7	Α	
Drain Current – Pulsed	I _{DM}	25	А	
Gate-Source Voltage	V_{GS}	±8.0	V	
Power Dissipation	P _D (T _a =25℃)	1.5	10/	
Power Dissipation	P _D (T _a =70°C)	1.0	W	
Junction-to-Ambient ^A	t ≤ 10s	Б	83	°C / \\/
Junction-to-Ambient ^{AD}	Steady-State	$R_{ hetaJA}$	120	°C/W
Junction-to-Lead	Steady-State	$R_{ heta JL}$	70	°C/W
Junction and Storage Temperatur	T _{j,} T _{stg}	-55 ~ 150	°C	

Electrical Characteristics($T_a=25$ °C)

Parameter	Symbol	Test Conditions		Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V I_D =250 μ A		20			V	
Drain-Source Leakage Current		V _{DS} =16V	$V_{GS}=0V$			1.0	μΑ	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =16V T _j =85℃	V _{GS} =0V			10	μA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} =±8V	V _{DS} =0V			±10	μΑ	
On state drain current	$I_{D(ON)}$	V _{GS} =4.5V	V _{DS} =5V	25			Α	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS}	I _D =250μA	0.45	0.6	1.0	V	
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V	I _D =6.0A		16	20	mΩ	
Static Drain-Source On-Resistance		V _{GS} =2.5V	$I_D=6.0A$		19	25	11122	
Forward Transconductance	g FS	V _{DS} =5.0V	I _D =7.0A		50		S	
Forward On Voltage	V _{SD}	V _{GS} =0V	I _S =1.0A			1.3	V	
Maximum Body-Diode Continuous Current	Is					2	Α	
Input Capacitance	C_{iss}				1295			
Output Capacitance	C _{oss}	V_{DS} =10V V_{GS} =0V f=1.0MHz			160		pF	
Reverse Transfer Capacitance	C_{rss}				87			



Electrical Characteristics(T_a=25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Gate resistance	R _g	V_{DS} =0V V_{GS} =0V f=1.0MHz		1.8		ΚΩ
Total Gate Charge	Q_g			10	14	
Gate Source Charge	Q_{gs}	V_{DS} =10V V_{GS} =4.5V I_{D} =7.0A		4.2		nC
Gate Drain Charge	Q_{gd}			2.6		
Turn-on Delay Time	t _{d(on)}			280		ns
Rise Time	t _r	V _{DS} =10V V _{GS} =4.5V		328		ns
Turn-off Delay Time	t _{d(off)}	$R_G=3.0\Omega$ $R_L=1.54\Omega$		3.76		μs
Fall Time	t _f			2.24		μs
Body Diode Reverse Recovery Time	t _{rr}	I _F =7A dI/dt=100A/ms V _{GS} =-9V		31		ns
Body Diode Reverse Recovery Charge	Q _{rr}	IF=7A dI/dt=100A/ms V _{GS} =-9V		6.8		nC

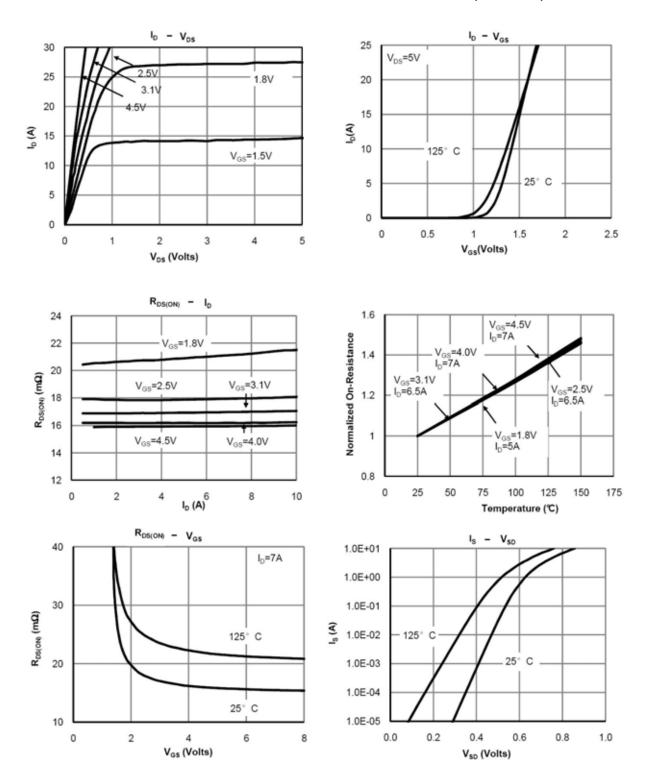
Notes:

A. The value of $R_{\theta JA}$ is measured with the device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

- B. The power dissipation P_D is based on $T_{J(MAX)}$ =150°C, using \leq 10s junction-to-ambient thermal resistance.
- C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300ms pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$ =150°C. The SOA curve provides a single pulse rating.

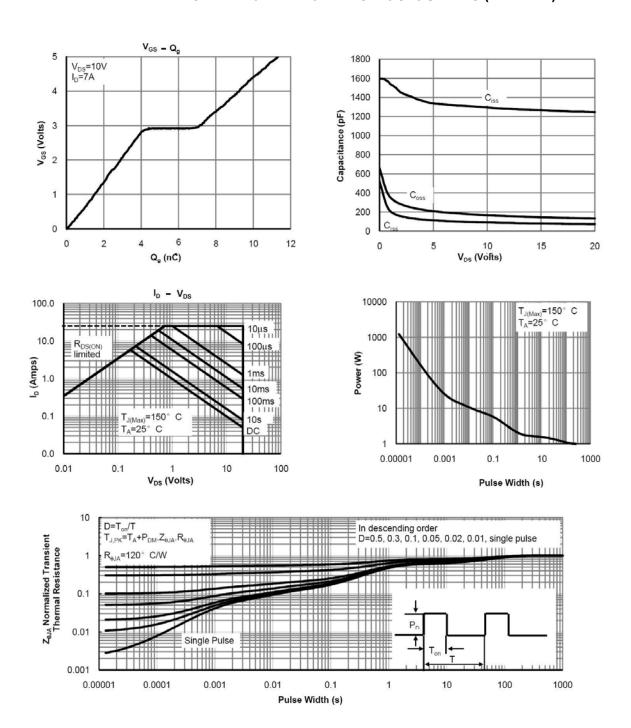


RATING AND CHARACTERISTICS CURVES (RM8810)



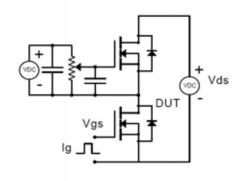


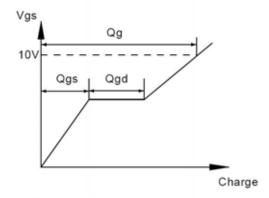
RATING AND CHARACTERISTICS CURVES (RM8810)



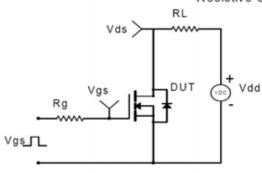


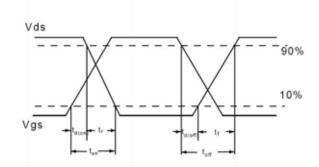
Test circuit and waveform



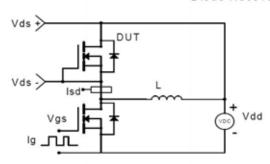


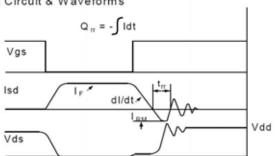
Resistive Switching Test Circuit & Waveforms





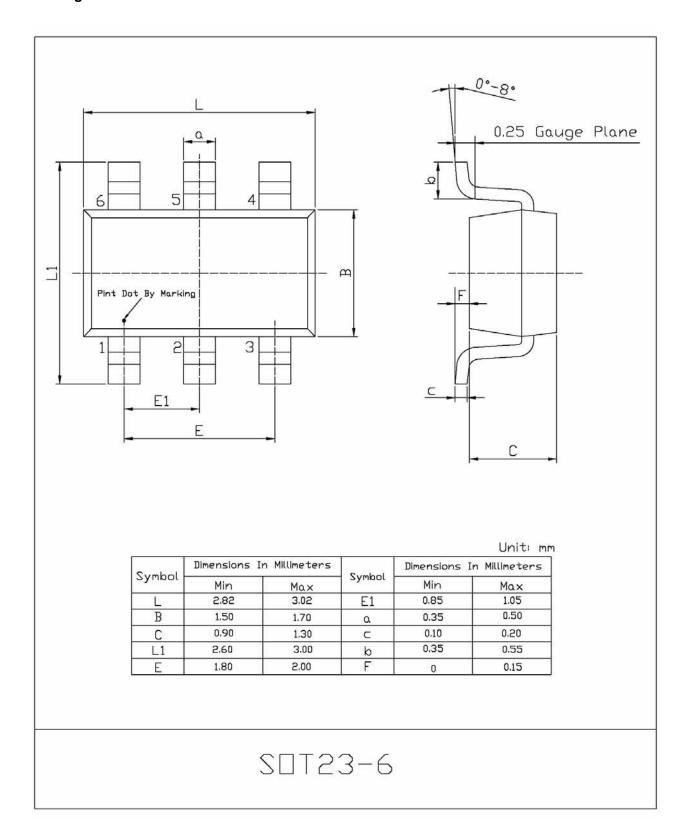
Diode Recovery Test Circuit & Waveforms



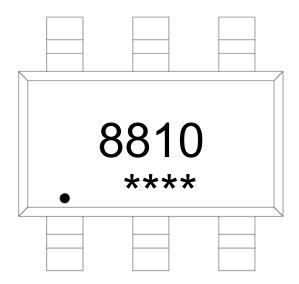




Package Dimensions



Marking Instructions



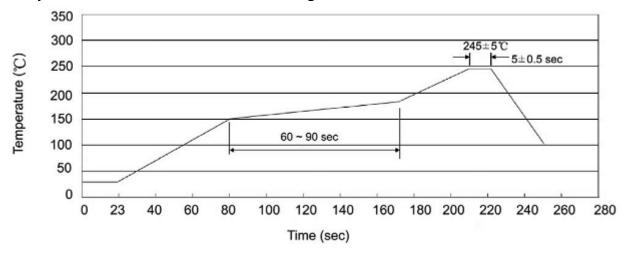
Note:

8810: Product Type.

****: Date code change with manufacturing date.



Temperature Profile for IR Reflow Soldering(Pb-Free)



Notes:

1.Preheating:25~150 °C, Time:60~90sec.

2.Peak Temp.:245 $\pm 5^{\circ}$ C, Duration:5 ± 0.5 sec.

3. Cooling Speed: 2~10°C/sec.

Resistance to Soldering Heat Test Conditions

Temp:260±5℃ Time:10±1 sec

Packaging SPEC.

REEL

Pac	ckage Type		Units				Dimension		(unit: mm ³)	
l acting type		Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box	
S	OT23-5/6	3,000	10	30,000	4	120,000	7″ ×8	210×205×205	445×230×435	



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